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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	51
Program Memory Size	192КВ (192К х 8)
Program Memory Type	FLASH
EEPROM Size	6K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l071rzt6tr

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 5. Functionalities depending on the working mode (from Run/active down to standby) (continued)⁽¹⁾⁽²⁾

			Low-	Low-	Stop	Ś	Standby	
IPs	Run/Active	Sleep	power run	power sleep	Wakeup capabilit	,	Wakeup capability	
	Down to 140 µA/MHz (from Flash memory)	Down to 37 µA/MHz (from Flash memory)	Down to		0.4 μA (No RTC) V _{DD} =1.8	0. / RTC	28 µA (No) V _{DD} =1.8 V	
Consumption $V_{-} = 1.8 \text{ to } 3.6 \text{ V}$				Down to 4.5 µA	0.8 μA (with RTC) V _{DD} =1.8 [•]	0.6 / RTC	5 μΑ (with) V _{DD} =1.8 V	
V _{DD} =1.8 to 3.6 V (Typ)			8 μΑ		0.4 μA (No RTC) V _{DD} =3.0 [•]	0. / RTC	29 µA (No) V _{DD} =3.0 V	
					1 μA (with RTC V _{DD} =3.0 V	0.8 RTC	85 μΑ (with) V _{DD} =3.0 V	

1. Legend:

"Y" = Yes (enable). "O" = Optional can be enabled/disabled by software) "-" = Not available

2. The consumption values given in this table are preliminary data given for indication. They are subject to slight changes.

- 3. Some peripherals with wakeup from Stop capability can request HSI to be enabled. In this case, HSI is woken up by the peripheral, and only feeds the peripheral which requested it. HSI is automatically put off when the peripheral does not need it anymore.
- 4. UART and LPUART reception is functional in Stop mode. It generates a wakeup interrupt on Start. To generate a wakeup on address match or received frame event, the LPUART can run on LSE clock while the UART has to wake up or keep running the HSI clock.
- 5. I2C address detection is functional in Stop mode. It generates a wakeup interrupt in case of address match. It will wake up the HSI during reception.

3.2 Interconnect matrix

Several peripherals are directly interconnected. This allows autonomous communication between peripherals, thus saving CPU resources and power consumption. In addition, these hardware connections allow fast and predictable latency.

Depending on peripherals, these interconnections can operate in Run, Sleep, Low-power run, Low-power sleep and Stop modes.

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low- power run	Low- power sleep	Stop
COMPx	TIM2,TIM21, TIM22	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	-
	LPTIM	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	Y
TIMx	TIMx	Timer triggered by other timer	Y	Y	Y	Y	-

Table 6.	STM32L0xx	peripherals	interconnect matrix
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3.6 Low-power real-time clock and backup registers

The real time clock (RTC) and the 5 backup registers are supplied in all modes including standby mode. The backup registers are five 32-bit registers used to store 20 bytes of user application data. They are not reset by a system reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. Its main features are the following:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatically correction for 28, 29 (leap year), 30, and 31 day of the month
- Two programmable alarms with wake up from Stop and Standby mode capability
- Periodic wakeup from Stop and Standby with programmable resolution and period
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- 2 anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 37 kHz)
- The high-speed external clock

3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated alternate function registers. All GPIOs are high current capable. Each GPIO output, speed can be slowed (40 MHz, 10 MHz, 2 MHz, 400 kHz). The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to a dedicated IO bus with a toggling speed of up to 32 MHz.

Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 29 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 84 GPIOs can be connected to the 16 configurable interrupt/event lines. The 13 other lines are connected to PVD, RTC, USARTs, I2C, LPUART, LPTIMER or comparator events.

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3.15.2 Universal synchronous/asynchronous receiver transmitter (USART)

The four USART interfaces (USART1, USART2, USART4 and USART5) are able to communicate at speeds of up to 4 Mbit/s.

They provide hardware management of the CTS, RTS and RS485 driver enable (DE) signals, multiprocessor communication mode, master synchronous communication and single-wire half-duplex communication mode. USART1 and USART2 also support SmartCard communication (ISO 7816), IrDA SIR ENDEC, LIN Master/Slave capability, auto baud rate feature and has a clock domain independent from the CPU clock, allowing to wake up the MCU from Stop mode using baudrates up to 42 Kbaud.

All USART interfaces can be served by the DMA controller.

Table 12 for the supported modes and features of USART interfaces.

USART modes/features ⁽¹⁾	USART1 and USART2	USART4 and USART5
Hardware flow control for modem	Х	Х
Continuous communication using DMA	Х	Х
Multiprocessor communication	Х	Х
Synchronous mode ⁽²⁾	Х	Х
Smartcard mode	Х	-
Single-wire half-duplex communication	Х	Х
IrDA SIR ENDEC block	Х	-
LIN mode	Х	-
Dual clock domain and wakeup from Stop mode	Х	-
Receiver timeout interrupt	Х	-
Modbus communication	Х	-
Auto baud rate detection (4 modes)	Х	-
Driver Enable	Х	Х

Table 12. USART implementation

1. X = supported.

2. This mode allows using the USART as an SPI master.

3.15.3 Low-power universal asynchronous receiver transmitter (LPUART)

The devices embed one Low-power UART. The LPUART supports asynchronous serial communication with minimum power consumption. It supports half duplex single wire communication and modem operations (CTS/RTS). It allows multiprocessor communication.

The LPUART has a clock domain independent from the CPU clock. It can wake up the system from Stop mode using baudrates up to 46 Kbaud. The Wakeup events from Stop mode are programmable and can be:

- Start bit detection
- Or any received data frame
- Or a specific programmed data frame



4 Pin descriptions



1. The above figure shows the package top view.

2. I/O supplied by VDDIO2.



48					Table 18. Alter	nate function	ns port C			
/136			AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
	Port		SPI1/SPI2/I2S2/ USART1/2/ LPUART1/ LPTIM1/ TIM2/21/22/ EVENTOUT/ SYS_AF	SPI1/SPI2/I2S2/I2C1/ TIM2/21	SPI1/SPI2/I2S2/ LPUART1/ USART5/ LPTIM1/TIM2/3 /EVENTOUT/SYS_AF	I2C1/ EVENTOUT	I2C1/USART1/2/ LPUART1/ TIM3/22/ EVENTOUT	SPI2/I2S2 /I2C2/ USART1/ TIM2/21/22	I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/E VENTOUT	I2C3/LPUART1/ COMP1/2/ TIM3
		PC0	LPTIM1_IN1		EVENTOUT				LPUART1_RX	I2C3_SCL
		PC1	LPTIM1_OUT		EVENTOUT				LPUART1_TX	I2C3_SDA
		PC2	LPTIM1_IN2		SPI2_MISO/ I2S2_MCK					
_		PC3	LPTIM1_ETR		SPI2_MOSI/ I2S2_SD					
) ocll		PC4	EVENTOUT		LPUART1_TX					
002		PC5			LPUART1_RX					
7101	o	PC6	TIM22_CH1		TIM3_CH1					
l Re	Port (PC7	TIM22_CH2		TIM3_CH2					
< 3		PC8	TIM22_ETR		TIM3_CH3					
		PC9	TIM21_ETR		TIM3_CH4					I2C3_SDA
		PC10	LPUART1_TX						USART4_TX	
		PC11	LPUART1_RX						USART4_RX	
		PC12			USART5_TX				USART4_CK	
		PC13								
		PC14								
		PC15								

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Power supply scheme 6.1.6



Figure 14. Power supply scheme

6.1.7 **Current consumption measurement**



Figure 15. Current consumption measurement scheme



Peripheral		Typical consumption, V _{DD} = 3.0 V, T _A = 25 °C					
		Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	Low-power sleep and run	Unit	
	GPIOA	3.5	3	2.5	2.5		
	GPIOB	3.5	2.5	2	2.5		
Cortex-	GPIOC	8.5	6.5	5.5	7	µA/MHz (f _{HCLK})	
I/O port	GPIOD	1	0.5	0.5	0.5		
	GPIOE	8	6	5	6		
	GPIOH	1.5	1	1	0.5		
	CRC	1.5	1	1	1		
AHB	FLASH	0 ⁽³⁾	0 ⁽³⁾	0 ⁽³⁾	0 ⁽³⁾	µA/MHz	
	DMA1	10	8	6.5	8.5	VIICLK/	
All enabled		204	162	130	202	µА/МНz (f _{HCLK})	
PWR		2.5	2	2	1	µA/MHz (f _{HCLK})	

Table 39. Peripheral current consumption in Run or Sleep mode(1) (continu

 Data based on differential I_{DD} measurement between all peripherals off an one peripheral with clock enabled, in the following conditions: f_{HCLK} = 32 MHz (range 1), f_{HCLK} = 16 MHz (range 2), f_{HCLK} = 4 MHz (range 3), f_{HCLK} = 64kHz (Low-power run/sleep), f_{APB1} = f_{HCLK}, f_{APB2} = f_{HCLK}, default prescaler value for each peripheral. The CPU is in Sleep mode in both cases. No I/O pins toggling. Not tested in production.

2. HSI oscillator is off for this measure.

3. Current consumption is negligible and close to 0 μ A.



Low-speed external user clock generated from an external source

The characteristics given in the following table result from tests performed using a lowspeed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 25*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LSE_ext}	User external clock source frequency		1	32.768	1000	kHz
V _{LSEH}	OSC32_IN input pin high level voltage		0.7V _{DD}	-	V _{DD}	V
V _{LSEL}	OSC32_IN input pin low level voltage	-	V _{SS}	-	0.3V _{DD}	v
t _{w(LSE)} t _{w(LSE)}	OSC32_IN high or low time		465	-	-	ne
t _{r(LSE)} t _{f(LSE)}	OSC32_IN rise or fall time		-	-	10	115
C _{IN(LSE)}	OSC32_IN input capacitance	-	-	0.6	-	pF
DuCy _(LSE)	Duty cycle	-	45	-	55	%
١L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	μA

Table 43. Low-speed external user clock characteristics⁽¹⁾

1. Guaranteed by design, not tested in production







Symbol	Parameter	Condition	Тур	Мах	Unit
		MSI range 0	0.75	-	
I _{DD(MSI)} ⁽²⁾		MSI range 1	1	-	
		MSI range 2	1.5	-	
	MSI oscillator power consumption	MSI range 3	2.5	-	μA
		MSI range 4	4.5	-	
		MSI range 5	8	-	
		MSI range 6	15	-	
		MSI range 0	30	-	
		MSI range 1	20	-	
		MSI range 2	15	-	
		MSI range 3	10	-	
	MSI oscillator startup time	MSI range 4	6	-	μs
^t su(msi)		MSI range 5	5	-	
		MSI range 6, Voltage range 1 and 2	3.5	-	
		MSI range 6, Voltage range 3	5	-	
		MSI range 0	-	40	
		MSI range 1	-	20	
		MSI range 2	-	10	
		MSI range 3	-	4	
t(2)	MSI oscillator stabilization time	MSI range 4	-	2.5	116
'STAB(MSI)		MSI range 5	-	2	μο
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
fourtheast	MSL oscillator frequency overshoot	Any range to range 5	-	4	МНт
'OVER(MSI)		Any range to range 6	-	6	

Table 48. MSI oscillator characteristics (continued)

1. This is a deviation for an individual part, once the initial frequency has been measured.

2. Guaranteed by characterization results.



Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit
I _{DD}	Average current during the whole programming / erase operation		-	500	700	μA
	Maximum current (peak) during the whole programming / erase operation	T _A = 25 °C, V _{DD} = 3.6 V	-	1.5	2.5	mA

 Table 51. Flash memory and data EEPROM characteristics

1. Guaranteed by design.

Cumhal	Deveneder	Conditions	Value	11
Symbol	Parameter	Conditions	Min ⁽¹⁾	Unit
	Cycling (erase / write) Program memory	T. – -40°C to 105 °C	10	
Novo ⁽²⁾	Cycling (erase / write) EEPROM data memory		100	kovoles
INCYC' /	Cycling (erase / write) Program memory	T. – -40°C to 125 °C	0.2	kcycles
	Cycling (erase / write) EEPROM data memory		2	
	Data retention (program memory) after 10 kcycles at T _A = 85 °C	T = +85 °C	30	
	Data retention (EEPROM data memory) after 100 kcycles at T _A = 85 °C	TRET - 100 O	30	
t(2)	Data retention (program memory) after 10 kcycles at T _A = 105 °C	T = +105 °C		Vears
^t RET ⁽²⁾	Data retention (EEPROM data memory) after 100 kcycles at T_A = 105 °C	TRET - 100 0	- 10	years
	Data retention (program memory) after 200 cycles at T _A = 125 °C	T = +125 °C		
	Data retention (EEPROM data memory) after 2 kcycles at T _A = 125 °C	REI - 123 0		

1. Guaranteed by characterization results.

2. Characterization is done according to JEDEC JESD22-A117.

6.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.



6.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $-5 \mu A/+0 \mu A$ range), or other functional failure (for example reset occurrence oscillator frequency deviation).

The test results are given in the Table 57.

		Functional s			
Symbol	Description	Negative injection	Positive injection	Unit	
I _{INJ}	Injected current on BOOT0	-0	NA		
	Injected current on PA0, PA4, PA5, PC15, PH0 and PH1	-5	0	mA	
	Injected current on any other FT, FTf pins	-5 ⁽¹⁾	NA		
	Injected current on any other pins	-5 ⁽¹⁾	+5		

Table 57. I/O current injection susceptibility

1. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.



Output voltage levels

Unless otherwise specified, the parameters given in *Table 59* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 25*. All I/Os are CMOS and TTL compliant.

Symbol	Parameter	Conditions	Min	Max	Unit
V _{OL} ⁽¹⁾	Output low level voltage for an I/O pin	CMOS port ⁽²⁾ ,		0.4	
V _{OH} ⁽³⁾	Output high level voltage for an I/O pin	$1_{O} - 40 \text{ mA}$ 2.7 V \leq V _{DD} \leq 3.6 V	V _{DD} -0.4	-	
V _{OL} ⁽¹⁾	Output low level voltage for an I/O pin	$\begin{array}{c} {\sf TTL \ port}^{(2)}, \\ {\sf I}_{IO} = + \ 8 \ mA \\ {\sf 2.7 \ V} \leq {\sf V}_{DD} \leq \ 3.6 \ {\sf V} \end{array}$	-	0.4	
V _{OH} ⁽³⁾⁽⁴⁾	Output high level voltage for an I/O pin	$\begin{array}{l} \text{TTL port}^{(2)},\\ \text{I}_{\text{IO}} \texttt{=} -6 \text{ mA}\\ 2.7 \text{ V} \leq \text{V}_{DD} \leq \ 3.6 \text{ V} \end{array}$	2.4	-	
V _{OL} ⁽¹⁾⁽⁴⁾	Output low level voltage for an I/O pin	I_{IO} = +15 mA 2.7 V \leq V _{DD} \leq 3.6 V	-	1.3	V
V _{OH} ⁽³⁾⁽⁴⁾	Output high level voltage for an I/O pin	$\begin{array}{l} \text{I}_{\text{IO}} \text{ = -15 mA} \\ \text{2.7 V} \leq \text{V}_{DD} \leq \ \text{3.6 V} \end{array}$	V _{DD} -1.3	-	
V _{OL} ⁽¹⁾⁽⁴⁾	Output low level voltage for an I/O pin	I_{IO} = +4 mA 1.65 V \leq V _{DD} < 3.6 V	-	0.45	
V _{OH} ⁽³⁾⁽⁴⁾	Output high level voltage for an I/O pin	I_{IO} = -4 mA 1.65 V \leq V _{DD} \leq 3.6 V	V _{DD} -0.45	-	
V _{OLFM+} ⁽¹⁾⁽⁴⁾	Output low level voltage for an FTf	$I_{IO} = 20 \text{ mA}$ 2.7 V \leq V _{DD} \leq 3.6 V	-	0.4	
	I/O pin in Fm+ mode	$\begin{array}{c} {\sf I}_{IO} = 10 \mbox{ mA} \\ 1.65 \mbox{ V} \leq {\sf V}_{DD} \leq \ 3.6 \mbox{ V} \end{array}$	-	0.4	

Table 59. Output voltage characteristics

 The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 23*. The sum of the currents sunk by all the I/Os (I/O ports and control pins) must always be respected and must not exceed ΣI_{IO(PIN)}.

2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.

3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in Table 23. The sum of the currents sourced by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.

4. Guaranteed by characterization results.



Figure 29. Recommended NRST pin protection

1. The reset network protects the device against parasitic resets.

The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 61*. Otherwise the reset will not be taken into account by the device. 2.

6.3.15 **12-bit ADC characteristics**

Unless otherwise specified, the parameters given in Table 62 are derived from tests performed under ambient temperature, f_{PCLK} frequency and $\mathsf{V}_{\mathsf{DDA}}$ supply voltage conditions summarized in Table 25: General operating conditions.

It is recommended to perform a calibration after each power-up. Note:

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit	
M	Analog supply voltage for	Fast channel	1.65	.65 - 3.6		V	
VDDA	ADC on	Standard channel	1.75 ⁽¹⁾	-	3.6		
V _{REF+}	Positive reference voltage	-	1.65		V _{DDA}	V	
V _{REF-}	Negative reference voltage	-	-	0	-		
	Current consumption of the	1.14 Msps	-	200	-		
	ADC on $V_{\mbox{DDA}}$ and $V_{\mbox{REF}^+}$	10 ksps	-	40	-		
IDDA (ADC)	Current consumption of the	1.14 Msps	-	70	-	μΑ	
	ADC on V _{DD} ⁽²⁾	10 ksps	-	1	-		
		Voltage scaling Range 1	0.14	-	16	MHz	
f _{ADC}	ADC clock frequency	Voltage scaling Range 2	0.14	-	8		
		Voltage scaling Range 3	0.14	-	4		
f _S ⁽³⁾	Sampling rate	12-bit resolution	0.01	-	1.14	MHz	
f _{TRIG} ⁽³⁾	External trigger frequency	f _{ADC} = 16 MHz, 12-bit resolution	-	-	941	kHz	
		-	-	-	17	1/f _{ADC}	
V _{AIN}	Conversion voltage range	-	0	-	V _{REF+}	V	
R _{AIN} ⁽³⁾	External input impedance	See <i>Equation 1</i> and <i>Table 63</i> for details	-	-	50	kΩ	
R _{ADC} ⁽³⁾⁽⁴⁾	Sampling switch resistance	-	-	-	1	kΩ	

Table 62. ADC characteristics



Equation 1: RAIN max formula

$$R_{AIN} < \frac{T_{S}}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The simplified formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

		R _{AIN} max for standard channels (kΩ)							
T _s (cycles)	t _S (μs)	fast channels (kΩ)	V _{DD} > 2.7 V	V _{DD} > 2.4 V	V _{DD} > 2.0 V	V _{DD} > 1.8 V	V _{DD} > 1.75 V	V _{DD} > 1.65 V and T _A > –10 °C	V _{DD} > 1.65 V and T _A > 25 °C
1.5	0.09	0.5	< 0.1	NA	NA	NA	NA	NA	NA
3.5	0.22	1	0.2	< 0.1	NA	NA	NA	NA	NA
7.5	0.47	2.5	1.7	1.5	< 0.1	NA	NA	NA	NA
12.5	0.78	4	3.2	3	1	NA	NA	NA	NA
19.5	1.22	6.5	5.7	5.5	3.5	NA	NA	NA	< 0.1
39.5	2.47	13	12.2	12	10	NA	NA	NA	5
79.5	4.97	27	26.2	26	24	< 0.1	NA	NA	19
160.5	10.03	50	49.2	49	47	32	< 0.1	< 0.1	42

Table 63. R_{AIN} max for f_{ADC} = 16 MHz⁽¹⁾

1. Guaranteed by design.

Table 64. ADC accuracy⁽¹⁾⁽²⁾⁽³⁾

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
ET	Total unadjusted error		-	2	4	
EO	Offset error		-	1	2.5	
EG	Gain error		-	1	2	LSB
EL	Integral linearity error		-	1.5	2.5	
ED	Differential linearity error		-	1	1.5	
	Effective number of bits	1.65 V < VDDA = VBEET < 3.6 V.	10.2	11		
ENOB	Effective number of bits (16-bit mode oversampling with ratio =256) ⁽⁴⁾	range 1/2/3	11.3	12.1	-	bits
SINAD	Signal-to-noise distortion		63	69	-	
	Signal-to-noise ratio		63	69	-	
SNR	Signal-to-noise ratio (16-bit mode oversampling with ratio =256) ⁽⁴⁾	ignal-to-noise ratio (16-bit mode versampling with ratio =256) ⁽⁴⁾		76	-	dB
THD	Total harmonic distortion		-	-85	-73	



Electrical characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Symbol	Farameter	conditions	IVIIII	чур	WIGA	Unit
ET	Total unadjusted error		-	2	5	
EO	Offset error		-	1	2.5	
EG	Gain error		-	1	2	LSB
EL	Integral linearity error]	-	1.5	3	
ED	Differential linearity error	1.65 V < V _{REF+} <v<sub>DDA < 3.6 V, range 1/2/3</v<sub>	-	1	2	
ENOB	Effective number of bits		10.0	11.0	-	bits
SINAD	Signal-to-noise distortion		62	69	-	
SNR	Signal-to-noise ratio		61	69	-	dB
THD	Total harmonic distortion		-	-85	-65	

Table 64. ADC accuracy⁽¹⁾⁽²⁾⁽³⁾ (continued)

1. ADC DC accuracy values are measured after internal calibration.

 ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.

Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in Section 6.3.12 does not affect the ADC accuracy.

3. Better performance may be achieved in restricted V_{DDA}, frequency and temperature ranges.

4. This number is obtained by the test board without additional noise, resulting in non-optimized value for oversampling mode.



Figure 30. ADC accuracy characteristics



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{scк}	SDI alaak fraguanay	Master mode			2	
1/t _{c(SCK)}	SFI Clock frequency	Slave mode	-	-	2 ⁽²⁾	
Duty _(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
t _{su(NSS)}	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	
t _{h(NSS)}	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-	
t _{w(SCKH)} t _{w(SCKL)}	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
t _{su(MI)}	Data input sotup timo	Master mode	1.5	-	-	
t _{su(SI)}	Data input setup time	Slave mode	6	-	-	
t _{h(MI)}	Data input hold time	Master mode	13.5	-	-	
t _{h(SI)}		Slave mode	16	-	-	ns
t _{a(SO}	Data output access time	Slave mode	30	-	70	
t _{dis(SO)}	Data output disable time	Slave mode	40	-	80	
t _{v(SO)}	Data output valid time	Slave mode	-	30	70	
t _{v(MO)}		Master mode	-	7	9	
t _{h(SO)}	Data output hold time	Slave mode	25	-	-	
t _{h(MO)}		Master mode	8	-	-	

				•	_	- ((1)
Table 74.	SPI	characteristics	in	voltage	Range	3 (, ı,

1. Guaranteed by characterization results.

2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while Duty_(SCK) = 50%.



Figure 34. SPI timing diagram - slave mode and CPHA = 0

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7.5 WLCSP49 package information



Figure 50. WLCSP49 - 49-pin, 3.294 x 3.258 mm, 0.4 mm pitch wafer level chip scale package outline

1. Drawing is not to scale.



Symbol	millimeters			inches(')				
Cymbol	Min	Тур	Мах	Min	Тур	Max		
A	0.525	0.555	0.585	0.0207	0.0219	0.0230		
A1	-	0.175	-	-	0.0069	-		
A2	-	0.380	-	-	0.0150	-		
A3 ⁽²⁾	-	0.025	-	-	0.0010	-		
b ⁽³⁾	0.220	0.250	0.280	0.0087	0.0098	0.0110		
D	3.259	3.294	3.329	0.1283	0.1297	0.1311		
E	3.223	3.258	3.293	0.1269	0.1283	0.1296		
е	-	0.400	-	-	0.0157	-		
e1	-	2.400	-	-	0.0945	-		
e2	-	2.400	-	-	0.0945	-		
F	-	0.447	-	-	0.0176	-		
G	-	0.429	-	-	0.0169	-		
aaa	-	-	0.100	-	-	0.0039		
bbb	-	-	0.100	-	-	0.0039		
CCC	-	-	0.100	-	-	0.0039		
ddd	-	-	0.050	-	-	0.0020		
eee	-	-	0.050	-	-	0.0020		

Table 82. WLCSP49 - 49-pin, 3.294 x 3.258 mm, 0.4 mm pitch wafer level chip scalepackage mechanical data

1. Values in inches are converted from mm and rounded to 4 decimal digits.

2. Back side coating

3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 51. WLCSP49 - 49-pin, 3.294 x 3.258 mm, 0.4 mm pitch wafer level chip scale recommended footprint





7.8 UFQFPN32 package information





^{1.} Drawing is not to scale.



Date	Revision	Changes
22-Mar-2016	3	Updated number of SPIs on cover page and in <i>Table 2: Ultra-low-power STM32L071xx device features and peripheral counts.</i> Changed minimum comparator supply voltage to 1.65 V on cover page. Added number of fast and standard channels in <i>Section 3.11:</i> <i>Analog-to-digital converter (ADC).</i> Updated <i>Section 3.15.2: Universal synchronous/asynchronous</i> <i>receiver transmitter (USART)</i> and <i>Section 3.15.4: Serial</i> <i>peripheral interface (SPI)/Inter-integrated sound (I2S)</i> to mention the fact that USARTs with synchronous mode feature can be used as SPI master interfaces. Added baudrate allowing to wake up the MCU from Stop mode in <i>Section 3.15.2: Universal synchronous/asynchronous receiver</i> <i>transmitter (USART)</i> and <i>Section 3.15.3: Low-power universal</i> <i>asynchronous receiver transmitter (LPUART)</i> . Changed V _{DDA} minimum value to 1.65 V in <i>Table 25: General</i> <i>operating conditions.</i> <i>Section 6.3.15: 12-bit ADC characteristics:</i> – <i>Table 62: ADC characteristics:</i> Distinction made between V _{DDA} for fast and standard channels; added note 1. Added note 4. related to R _{ADC} . Updated f _{TRIG} and V _{AIN} maximum value. Updated t _S and t _{CONV} . Added V _{REF+} . – Updated equation 1 description. – Updated <i>Table 63: RAIN max for fADC = 16 MHz</i> for f _{ADC} = 16 MHz and distinction made between fast and standard channels.

Table 89. Document revision history

